

METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE INCLUDING A
MONOCRYSTALLINE METAL OXIDE INTERFACE WITH SILICON

Abstract of the Disclosure

A method of fabricating a semiconductor structure including the steps of providing a silicon substrate (10) having a surface (12), forming on the surface (12) of the silicon substrate (10), by atomic layer deposition (ALD), a monocrystalline seed layer (20;21') comprising a silicate material and forming, by atomic layer deposition (ALD) one or more layers of a monocrystalline high dielectric constant oxide (42) on the seed layer (20;21').